

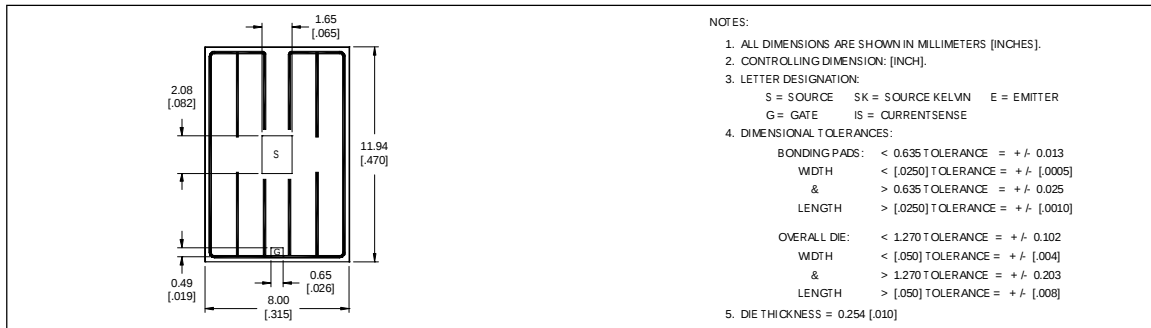
Electrical Characteristics

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500V Min.	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	0.090Ω Max.	$V_{GS} = 10V, I_D = 28A$
$V_{GS(th)}$	Gate Threshold Voltage	3.0V Min., 5.0V Max.	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	50μA Max.	$V_{DS} = 500V, V_{GS} = 0V, T_J = 25^\circ C$
I_{GSS}	Gate-to-Source Leakage Current	± 100nA Max.	$V_{GS} = \pm 30V$
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55°C to 150°C Max.	

Mechanical Data

Nominal Back Metal Composition, Thickness:	Cr-NiV-Ag (0.1μm-0.2μm-0.5μm)
Nominal Front Metal Composition, Thickness:	Al with 1% Si (0.004 mm)
Dimensions:	0.315" x 0.470" [8.00 mm x 11.94 mm]
Wafer Diameter:	150 mm
Wafer Thickness:	0.375 mm ± 0.025 mm
Relevant Die Mechanical Drawing Number	01-5444
Minimum Street Width	0.004"
Reject Ink Dot Size	0.005" Diameter Minimum
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination
Recommended Die Attach Conditions:	For optimum electrical results, die attach temperature should not exceed 300 °C
Referenced Package Part:	IRFPS43N50K

Die Outline



* Notes: Electrical characteristics are reported for the reference packaged part (see above) and cannot guaranteed in die sales form due to variations in packaging materials, dimension.